

**SINGLE-PHASE GLASS PASSIVATED  
SILICON BRIDGE RECTIFIER**

**VOLTAGE 1200 Volts CURRENT 1.0 Ampere**

**FEATURES**

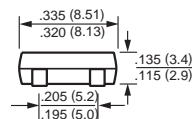
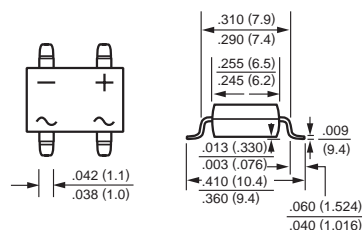
- \* Surge overload rating - 50 amperes peak
- \* Ideal for printed circuit board
- \* Reliable low cost construction utilizing molded
- \* Glass passivated device
- \* Polarity symbols molded on body
- \* Mounting position: Any
- \* Weight: 1.0 gram

**MECHANICAL DATA:**

- \* Epoxy : UL flammability classification 94V-0



**DB-S**



Dimensions in inches and (millimeters)

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Ratings at 25 °C ambient temperature unless otherwise specified.  
Single phase, half wave, 60 Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

**MAXIMUM RATINGS** (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	DB1012S	UNITS
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	1200	Volts
Maximum RMS Bridge Input Voltage	V <sub>RMS</sub>	840	Volts
Maximum DC Blocking Voltage	V <sub>DC</sub>	1200	Volts
Maximum Average Forward Output Current at TA = 40°C	I <sub>O</sub>	1.0	Amps
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	I <sub>FSM</sub>	50	Amps
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to + 150	°C

**ELECTRICAL CHARACTERISTICS** (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	DB1012S	UNITS
Maximum Forward Voltage Drop per Bridge Element at 1.0A DC	V <sub>F</sub>	1.1	Volts
Maximum Reverse Current at rated	I <sub>R</sub>	5.0	µAmps
DC Blocking Voltage per element			

NOTE: Suffix "-s" Surface Mount for Dip Bridge.

# RATING AND CHARACTERISTIC CURVES OF DB1012S

FIG. 1 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

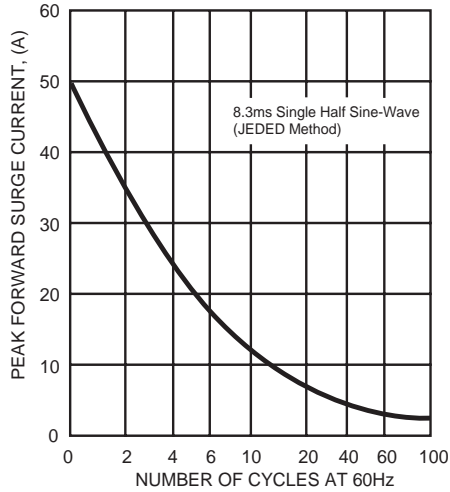


FIG. 2 - TYPICAL FORWARD CURRENT DERATING CURVE

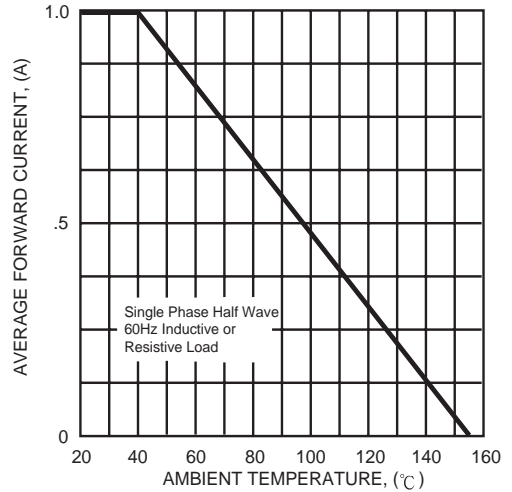


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

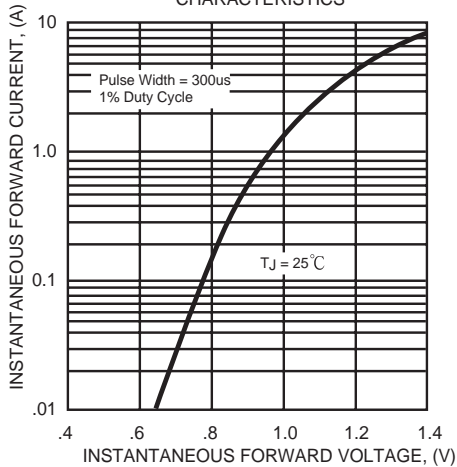


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS

